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HEMT High Power Amplifier



Rev_1-02

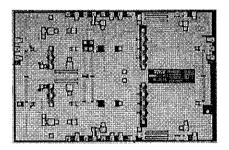
Features

♥ RF Frequency: 24.5 to 26.5 GHz

₩ Linear gain: 13 dB, typical

▼P1dB: 28 dBm, typical

♥ IP3: 37 dBm, typical



▼ Unconditionally Stable

▼ Excellent input and output VSWR

♥ DC Power: 5.0 Vdc at 1080 mA

Description and Application

The APH328C monolithic HEMT amplifier, a broadband, two-stage power device, is designed for use in commercial digital radios and wireless LANs. The balanced designed provides unconditional stability as well as excellent input and output VSWR. To ensure rugged and reliable operation, HEMT devices are fully passivated. Both bond pad and backside metallization are Ti/Au, which is compatible with conventional die attach, thermocompression, and thermosonic wire bonding assembly techniques.

Performance Characteristics (Ta = 25°C)

Min	Тур	Max ·	Unit
24.5		26.5	GHz
11	13		dB
26.5	28		dBm
	37		dBm
12	15		dΒ
12	15		dB
	5		V
	-0.4		V
	180		mΑ
	180		mΑ
	360		mA
	360		mA
	24.5 11 26.5 12	24.5 11 13 26.5 28 37 12 15 12 15 5 -0.4 180 360	24.5 26.5 11. 13 26.5 28 37 12. 15 12. 15 5 -0.4 -180 180 360

Absolute Maximum Ratings (Ta = 25°C)

Parameter	Min	Max	Unit
Vd1, Vd1A		6	· V
Vd2, Vd2A			
ld1		270	mA
ld1A		270	mA
ld2		540	mA
ld2A		540	mA
Vg1, Vg1A	-1	+0.3	V
Vg2, Vg2A			
Input drive level		18	dBm
Assy. Temperature		300	deg. C
(60 seconds)			





Product Datasheet

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Measured Performance Characteristics (Typical Performance at 25°C) Vd = 5 V, Id = 1080 mA

Freq GHz	S11 Mag	S11 Ang	S21 Mag	S21 Ang	\$12 Mag	S12 Ang	S22 Mag	S22 Ang
23.5	0.14	144,36	4.74	88.71	0.01	45.64	0.05	-140.39
23.8	0.14	138.17	4.95	74,58	0.00	19,47	0.05	-143.81
24.0	0.15	133.46	5.09	60.01	0.00	3.01	80.0	-151.55
24.3	0.15	127.28	5.21	44.40	0.00	9.90	0.08	-157.41
24.5	0.15	122.08	5.20	28.14	0.00	-16.65	0.11	-160.54
24.8	0.15	117.43	5.26	13.06	0.01	-15.31	0.12	-167.85
25.0	0.15	114.21	5.42	-2.46	0.00	-31.15	0.13	+175.70
25.3	0.15	109,44	5.44	-18.44	0.01	-50.99	0.14	171.45
25.5	0.15	107.29	5.34	-34.83	0.00	-56.50	0.15	162.53
25.8	0.15	103.26	5.11	-50.94	0.00	-69.23	0.14	151.72
26.0	0.14	100,45	5.09	-66.61	0.00	-86,41	0.14	143.77
26.3	0.14	96.72	5.00	-81.97	0.00	-86.12	0.13	133.08
26.5	0.13	94,23	4.86	-97,41	0.00	-128.03	0.13	126.35

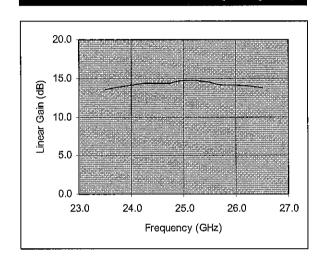
APH328C HEMT High Power Amplifier



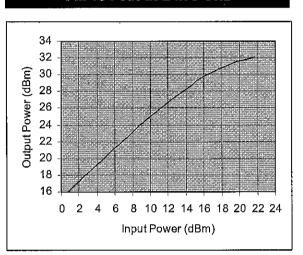
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Measured Performance Characteristics (Typical Performance at 25°C) Vd = 5 V, Id = 1000 mA

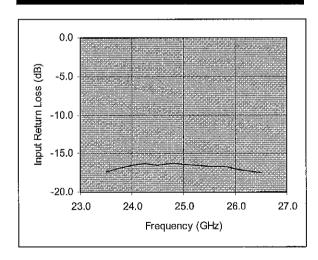
Pulsed Gain Versus Frequency



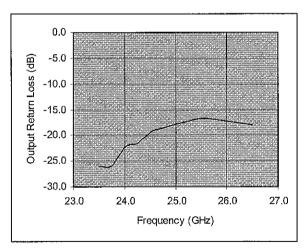
Pin vs Pout at 24.75 GHz



Input Return Loss Versus Frequency

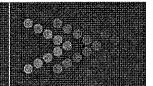


Output Return Loss Versus Frequency



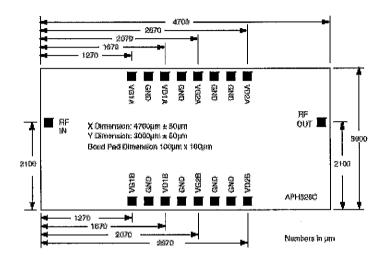
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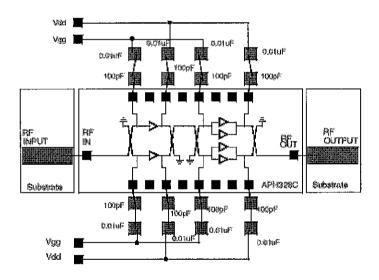


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Die Size and Bond Pad Locations



Suggested Bonding Arrangement



Recommended Assembly Notes

- 1. Bypass caps should be 100 pF ceramic (single-layer) placed no further than 30 mils from the amplifier.
- 2. Best performance obtained from use of <10 mil (long) by 3 by 0.5 mil ribbons on input and output.